

APT10M25BNR 100V 75A 0.025Ω
APT10M30BNR 100V 75A 0.030Ω

POWER MOS IV®

AVALANCHE RATED

N-CHANNEL ENHANCEMENT MODE LOW VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT10M25BNR	APT10M30BNR	UNIT
V_{DSS}	Drain-Source Voltage	100	100	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	75	75	Amps
I_{DM}	Pulsed Drain Current ^①	300	300	
V_{GS}	Gate-Source Voltage Continuous	±20		Volts
V_{GSM}	Gate-Source Voltage Transient	±30		
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	360		Watts
	Linear Derating Factor	2.9		W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150		°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300		
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	75		Amps
E_{AR}	Repetitive Avalanche Energy ^①	30		mJ
E_{AS}	Single Pulse Avalanche Energy ^④	1500		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 1.0mA$)	100			Volts
$I_D(ON)$	On State Drain Current ^② ($V_{DS} > I_D(ON) \times R_{DS}(ON)$ Max, $V_{GS} = 10V$)	APT10M25BNR	75		Amps
		APT10M30BNR	75		
$R_{DS}(ON)$	Drain-Source On-State Resistance ^② ($V_{GS} = 10V, 0.5 I_D$ [Cont.])	APT10M25BNR		0.025	Ohms
		APT10M30BNR		0.030	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V$)			250	µA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 20V, V_{DS} = 0V$)			±100	nA
$V_{GS}(TH)$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1.0mA$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.34	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS

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Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		5500	6500	pF
C_{oss}	Output Capacitance			2000	2800	
C_{rss}	Reverse Transfer Capacitance			760	1050	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		190	260	nC
Q_{gs}	Gate-Source Charge			48	75	
Q_{gd}	Gate-Drain ("Miller") Charge			85	120	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 1.8\Omega$		20	30	ns
t_r	Rise Time			90	130	
$t_{d(off)}$	Turn-off Delay Time			100	150	
t_f	Fall Time			75	120	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT10M25BNR		75	Amps
		APT10M30BNR		75	
I_{SM}	Pulsed Source Current ① (Body Diode)	APT10M25BNR		300	Amps
		APT10M30BNR		300	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$)			1.75	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)	100	200	400	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)	0.7	1.4	2.8	μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1 \text{ Sec.}$	360			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}], V_{DS} = P_D / I_D [\text{Cont.}], t = 1 \text{ Sec.}$	360			
I_{LM}	Inductive Current Clamped	APT10M25BNR	300			Amps
		APT10M30BNR	300			

① Repetitive Rating: Pulse width limited by maximum junction temperature.

③ See MIL-STD-750 Method 3471

④ Starting $T_J = 25^\circ\text{C}$, $L = 533\mu\text{H}$, $R_G = 25\Omega$, Peak $I_L = 75A$

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

APT Reserves the right to change, without notice, the specifications and information contained herein.

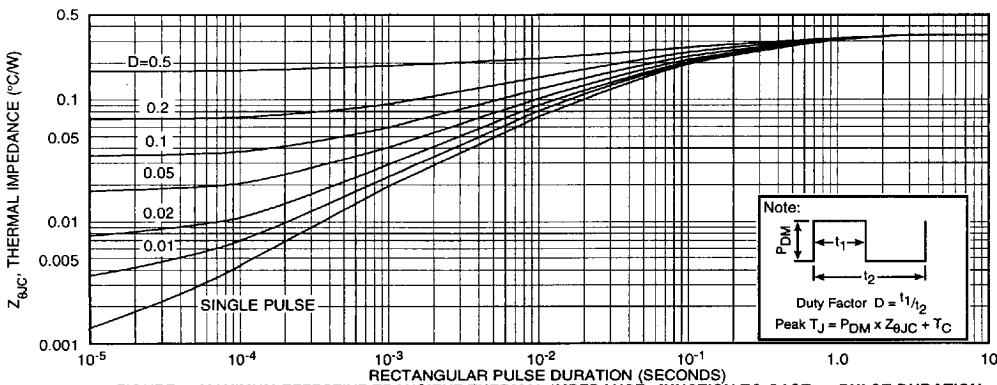


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

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APT10M25/10M30BNR

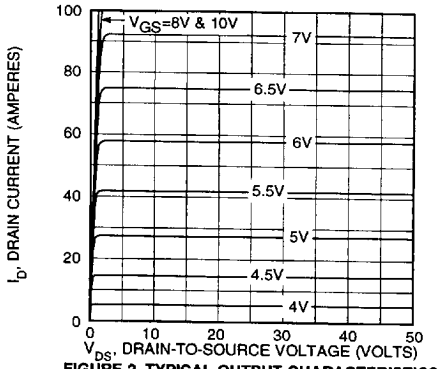


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

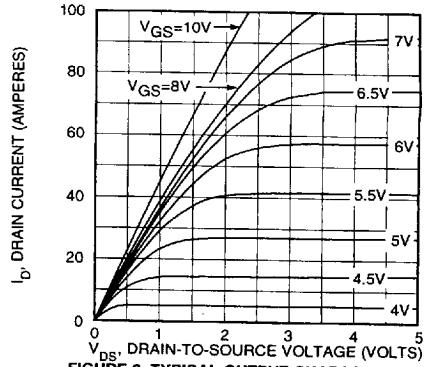


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

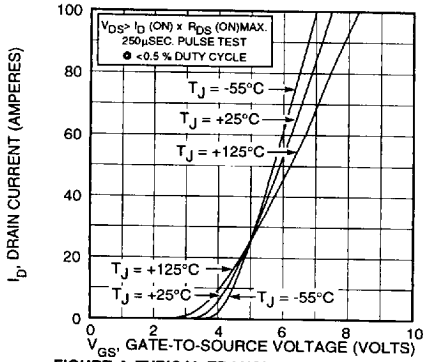


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

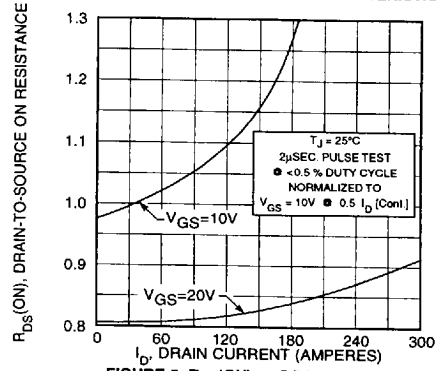


FIGURE 5, R_DS(ON) vs DRAIN CURRENT

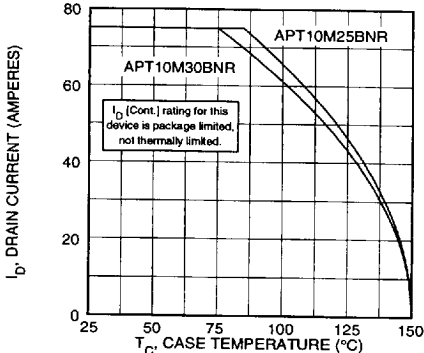


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

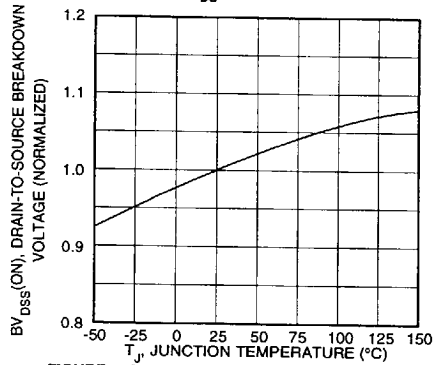


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

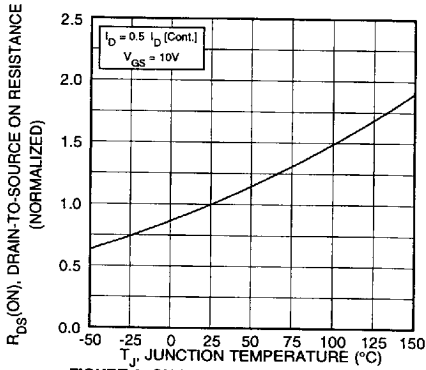


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

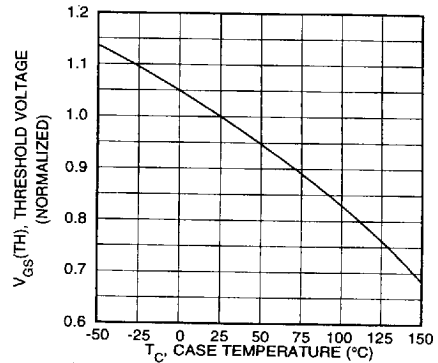


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

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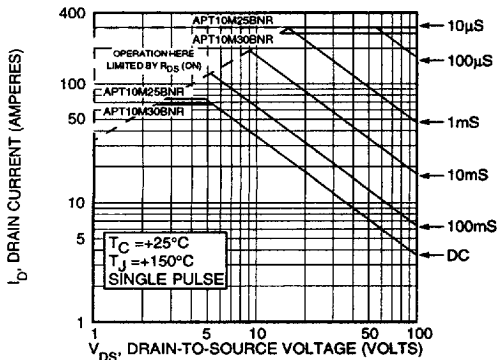


FIGURE 10, MAXIMUM SAFE OPERATING AREA

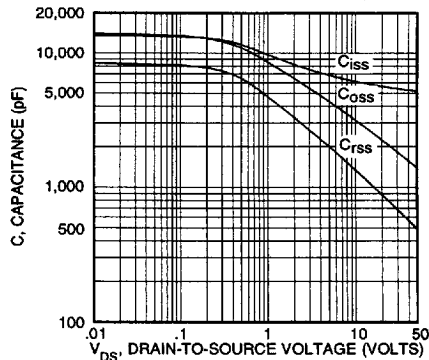


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

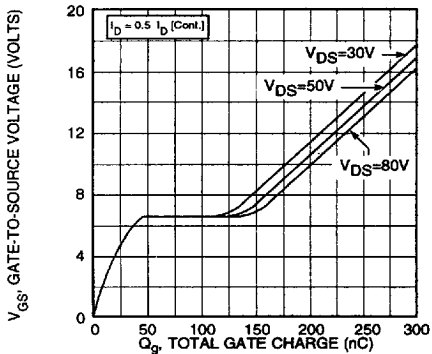


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

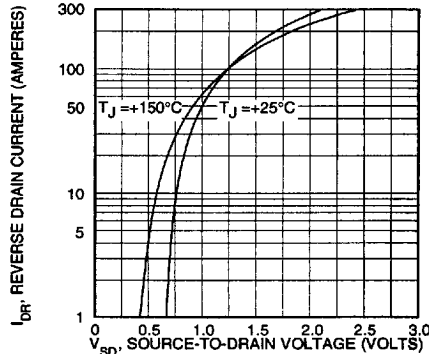
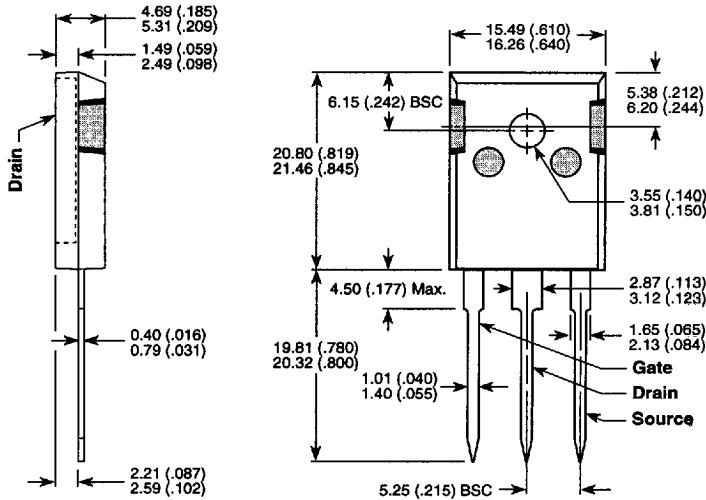


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247AD Package Outline



Dimensions in Millimeters and (Inches)
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